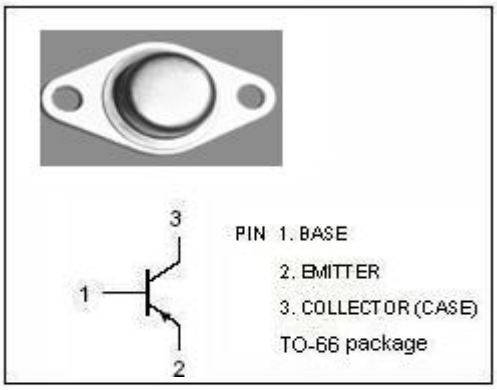
isc Silicon PNP Power Transistor 2N6213

DESCRIPTION

- High Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= -350V(Min)
- Good Linearity of h_{FE}
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

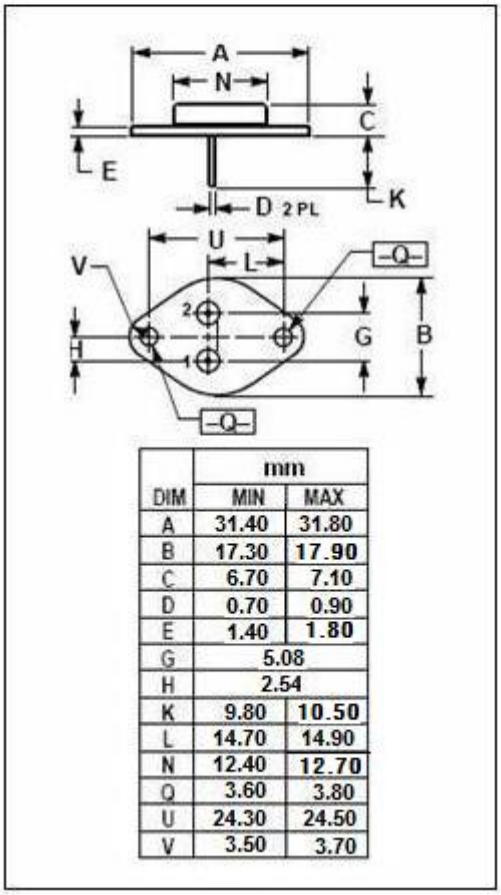


APPLICATIONS

- Designed for high-speed switching and linear amplifier application for high-voltage operational amplifier, switching regulators, converters, inverters,deflection stages and high fidelity amplifiers.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-400	V
V_{CEO}	Collector-Emitter Voltage	-350	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-5	A
I_B	Collector Current-Continuous	-1	A
P_C	Collector Power Dissipation @ T_C=25℃	35	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.90
C	6.70	7.10
D	0.70	0.90
E	1.40	1.80
G	5.08	
H	2.54	
K	9.80	10.50
L	14.70	14.90
N	12.40	12.70
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	5.0	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -50mA ; I_B= 0	-350			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Vltage	I_E= -1mA ; I_C= 0	-6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -1A; I_B= -125mA			-2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -1A; I_B= -125mA			-1.4	V
I_{CEV}	Collector Cutoff Current	V_{CE}= -360V; $V_{BE(off)}$= -1.5V			-0.5	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= -150V; I_B= 0			-5.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -6V; I_C= 0			-0.5	mA
h_{FE}	DC Current Gain	I_C= -1A ; V_{CE}= -4V	10		100	
f_T	Current-Gain—Bandwidth Product	I_C= -0.2A ;V_{CE}= -10V,f_{test}= 5MHz	10			MHz
C_{OB}	Output Capacitance	I_E=0;V_{CB}= -10V;f_{test}= 1MHz			220	pF
Switching times						
t_r	Rise Time	I_C= -1A , V_{CC}= -200V; I_{B1}= -I_{B2}= -125mA			0.6	μs
t_s	Storage Time				2.5	μs
t_f	Fall Time				0..6	μs